

GS5ABF - GS5MBF SURFACE MOUNT SILICON RECTIFIER DIODES

VOLTAGE RANGE: 50 - 1000V CURRENT: 5.0 A

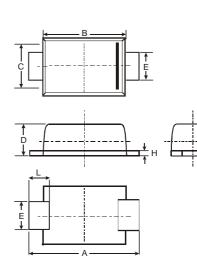
Features

- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Voltage Drop
- Low Power Loss
- Built-in Strain Relief
- Plastic Case Material has UL Flammability Classification Rating 94V-O

Mechanical Data

- Case:SMBF , Molded Plastic
- Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch
- Marking: Type Number
- Weight: 0.0018 ounces, 0.05grams





SMBF									
Dim	Min	Max	Тур						
Α	5.45	5.55	5.50						
В	4.27	4.33	4.30						
С	3.57	3.63	3.60						
D	1.32	1.38	1.35						
Ε	1.96	2.00	1.98						
Н	0.019	0.021	0.20						
L	0.73	0.77	0.75						
All Dimensions in mm									

Maximum Ratings and Electrical Characteristics T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	GS5ABF	GS5BBF	GS5DBF	GS5GBF	GS5JBF	GS5KBF	GS5MBF	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vrrm Vrwm Vr	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	VR(RMS)	35	70	140	280	420	560	700	V
Average Rectified Output Current $@T_L = 75^{\circ}C$	lo	5.0							А
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	100							A
Forward Voltage $@I_F = 5.0A$	Vfm	1.15						V	
Peak Reverse Current $@T_A = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_A = 125^{\circ}C$	Iгм	IRм 10 250						μA	
Typical Junction Capacitance (Note 1)	Cj	40							pF
Typical Thermal Resistance (Note 2)	R∉JL	10							°C/W
Operating and Storage Temperature Range	Tj, TSTG	-65 to +150							°C

Note: 1. Measured at 1.0 MHz and applied reverse voltage of 4.0 V DC.

2. Mounted on P.C. Board with 8.0mm² land area.



